

## The read-out ASIC for silicon drift detectors

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The paper describes the read-out ASIC for silicon X-ray drift detectors. The ASIC has been designed in CMOS 0.35  $\mu\text{m}$  technology and contained two read-out channels. Each channel include preamplifier and shaper. Preamplifiers optimized for operation with detectors, having capacitances of 100 fF. The 6-th order shaper have a controllable time constants (0.5 – 8  $\mu\text{s}$ ).

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